

## Silicon NPN Power Transistors

BU908

## DESCRIPTION

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- With TO-3PN package
- High voltage
- High speed switching

## APPLICATIONS

- For color TV horizontal deflection circuits.

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

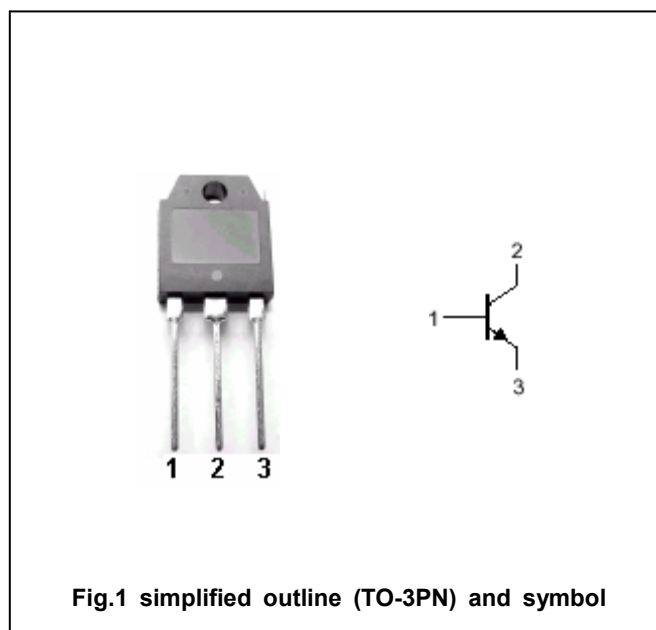


Fig.1 simplified outline (TO-3PN) and symbol

## Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	700	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		8	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> =25°C	125	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~150	°C

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance junction case	1.0	°C/W

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## CHARACTERISTICS

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 $T_j=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=100\text{mA}; I_B=0;$	700			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10\text{mA}; I_C=0;$	7			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C=3.2\text{A}; I_B=0.8\text{A}$			2.0	V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C=3.2\text{A}; I_B=0.8\text{A}$			1.3	V
$I_{CBO}$	Collector cut-off current	$V_{CB}=1500\text{V}; I_E=0$			1.0	mA
$I_{EBO}$	Emitter cut-off current	$V_{EB}=5\text{V}; I_C=0$			0.1	mA
$h_{FE}$	DC current gain	$I_C=1.5\text{A}; V_{CE}=5\text{V}$	8			
$f_T$	Transition frequency	$I_E=0; V_{CB}=10\text{V}; f=1\text{MHz}$		7		MHz

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PACKAGE OUTLINE

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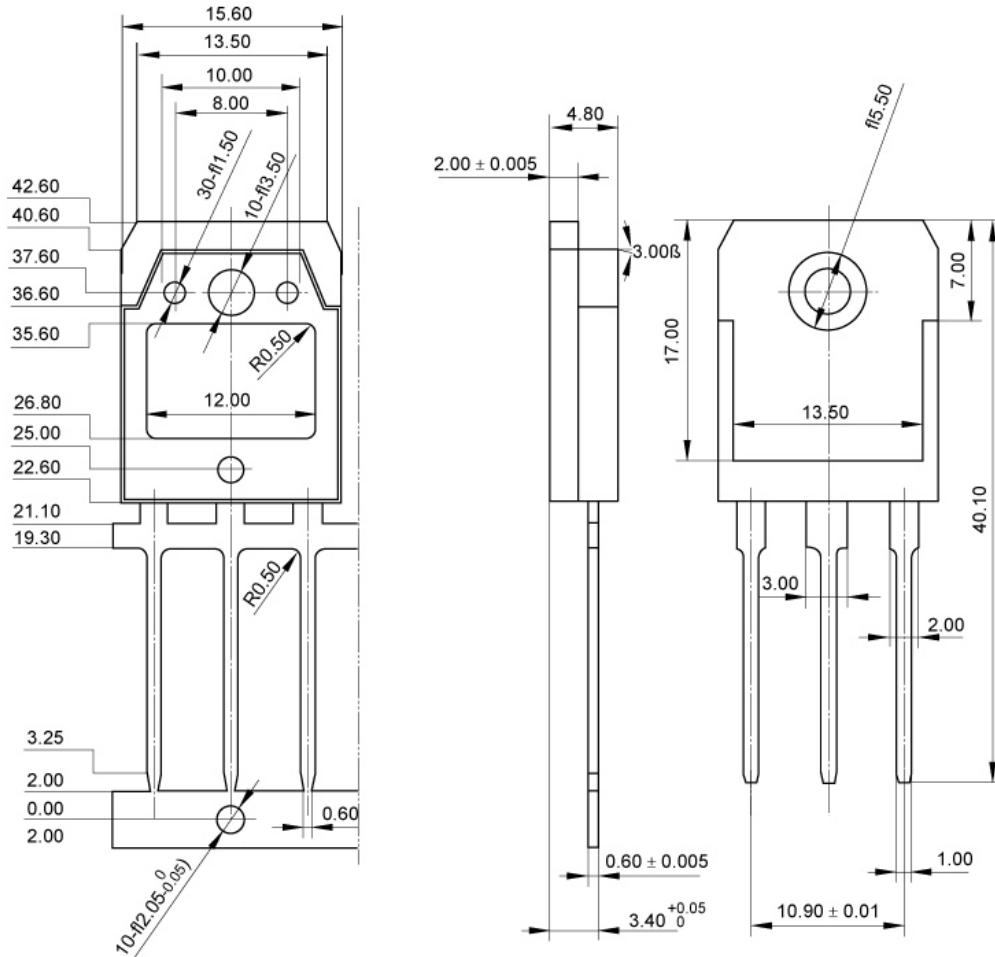


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)